



GP20A - GP20M

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V

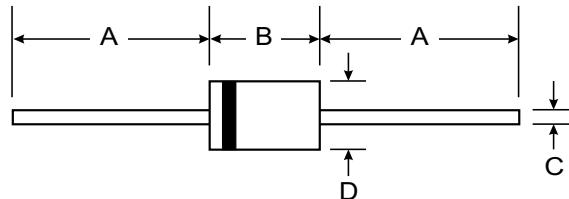
CURRENT: 2.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: D O - 15
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-15		
Dim	Min	Max
A	25.40	—
B	5.50	7.62
C	0.686	0.889
D	2.60	3.60

All Dimensions in mm

Maximum Ratings and Electrical Characteristics

T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GP20A	GP20B	GP20D	GP20G	GP20J	GP20K	GP20M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _R RM V _R WM V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _R (RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 75°C	I _O				2.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				70				A
Forward Voltage @I _F = 2.0A	V _{FM}				1.0				V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}				5.0 50				µA
Typical Junction Capacitance (Note 2)	C _j				20				pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}				40				K/W
Operating Temperature Range	T _j				-65 to +125				°C
Storage Temperature Range	T _{STG}				-65 to +150				°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

